

Single N-channel MOSFET

ELM4N0008FUA-S

<http://www.elm-tech.com>

■ General description

ELM4N0008FUA-S uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate threshold voltage.

■ Features

- $V_{ds}=100V$
- $I_d=2.2A$
- $R_{ds(on)} = 310m\Omega$ ($V_{gs}=10V$)
- $R_{ds(on)} = 320m\Omega$ ($V_{gs}=4.5V$)

■ Maximum absolute ratings

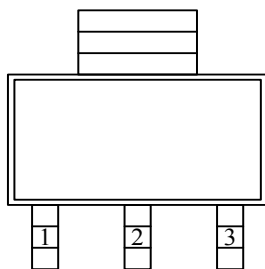
Parameter	Symbol	Limit	Unit	Note	
Drain-source voltage	V_{ds}	100	V		
Gate-source voltage	V_{gs}	± 20	V		
Continuous drain current ($V_{gs}=10V$)	I_d	$T_a=25^\circ C$	2.2	A	1
		$T_a=70^\circ C$	1.7		
Pulsed drain current	I_{dm}	5.5	A	2	
Power dissipation	P_d	1.5	W	3	
Storage temperature range	T_{stg}	-55 to 150	$^\circ C$		
Operating junction temperature range	T_j	-55 to 150	$^\circ C$		

■ Thermal characteristics

Parameter	Symbol	Typ.	Max.	Unit	Note
Thermal resistance junction-to-ambient	$R_{\theta ja}$	-	85	$^\circ C/W$	1
Thermal resistance junction-to-case	$R_{\theta jc}$	-	36	$^\circ C/W$	1

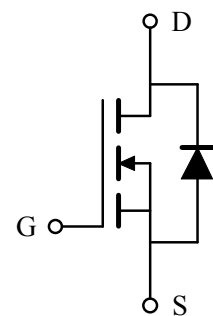
■ Pin configuration

SOT-223(TOP VIEW)



Pin No.	Pin name
1	GATE
2	DRAIN
3	SOURCE

■ Circuit



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■Electrical characteristics

T_j=25°C. Unless otherwise noted.

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BV _{dss}	I _d =250μA, V _{gs} =0V	100	-	-	V	
Drain-source leakage current	I _{dss}	V _{ds} =80V, V _{gs} =0V	-	-	1	μA	
		V _{ds} =80V, V _{gs} =0V, T _j =55°C	-	-	5		
Gate-body leakage current	I _{gss}	V _{ds} =0V, V _{gs} =±20V	-	-	±100	nA	
Gate threshold voltage	V _{gs(th)}	V _{ds} =V _{gs} , I _d =250μA	1.0	1.5	2.5	V	
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =10V, I _d =2A	-	260	310	mΩ	2
		V _{gs} =4.5V, I _d =1A	-	270	320		
Forward transconductance	G _{fs}	V _{ds} =5V, I _d =2A	-	2.4	-	S	
Diode forward voltage	V _{sd}	I _s =1A, V _{gs} =0V	-	-	1.2	V	2
Max. body-diode continuous current	I _s	V _{gs} =V _{ds} =0V, Force current	-	-	2.2	A	1, 4
Pulsed body-diode current	I _{sm}		-	-	5.5	A	2, 4
DYNAMIC PARAMETERS							
Input capacitance	C _{iss}	V _{gs} =0V, V _{ds} =15V, f=1MHz	-	510	711	pF	
Output capacitance	C _{oss}		-	30	41	pF	
Reverse transfer capacitance	C _{rss}		-	16	23	pF	
Gate resistance	R _g	V _{ds} =0V, V _{gs} =0V, f=1MHz	-	2.8	5.6	Ω	
SWITCHING PARAMETERS							
Total gate charge (10V)	Q _g	V _{gs} =10V, V _{ds} =50V, I _d =2A	-	9.3	12.7	nC	
Gate-source charge	Q _{gs}		-	2.0	2.8	nC	
Gate-drain charge	Q _{gd}		-	1.5	2.0	nC	
Turn-on delay time	t _{d(on)}	V _{gs} =10V, V _{ds} =50V, I _d =2A	-	2.0	4.0	ns	
Turn-on rise time	t _r		-	21.6	39.0	ns	
Turn-off delay time	t _{d(off)}	R _{gen} =3.3Ω	-	11.2	22.0	ns	
Turn-off fall time	t _f		-	18.8	37.6	ns	
Reverse recovery time	t _{rr}	I _f =2A, di/dt=100A/μs	-	17.5	-	ns	
Reverse recovery charge	Q _{rr}		-	14.0	-	nC	

NOTE :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300μs and duty cycle ≤ 2%.
3. The power dissipation is limited by 150°C junction temperature.
4. The data is theoretically the same as I_d and I_{dm}, in real applications, should be limited by total power dissipation.

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■ Typical characteristics

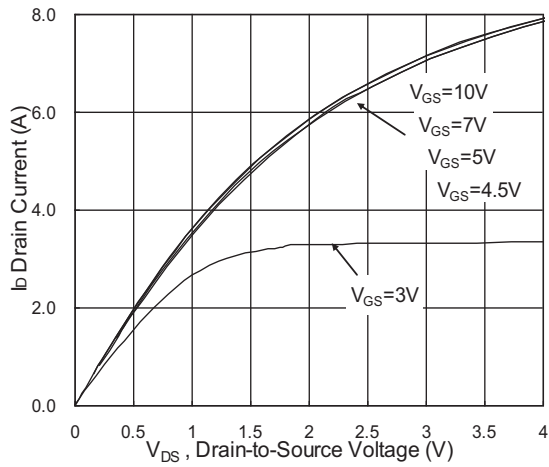


Fig.1 Typical Output Characteristics

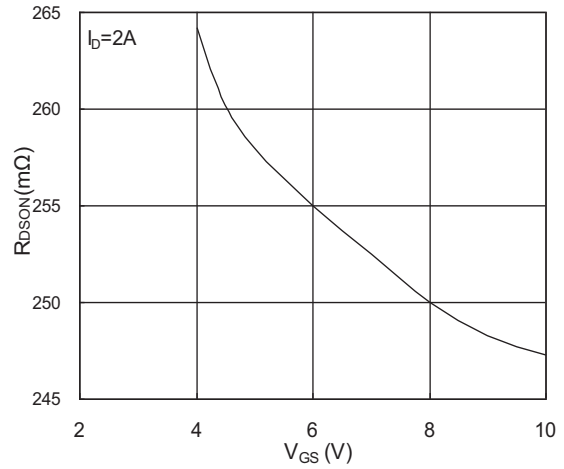


Fig.2 On-Resistance vs. Gate-Source

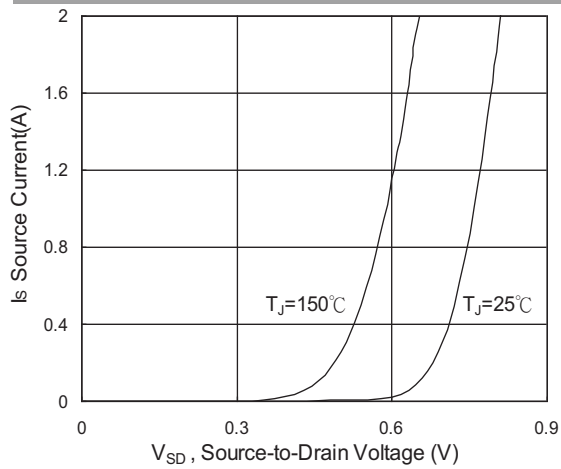


Fig.3 Forward Characteristics of Reverse

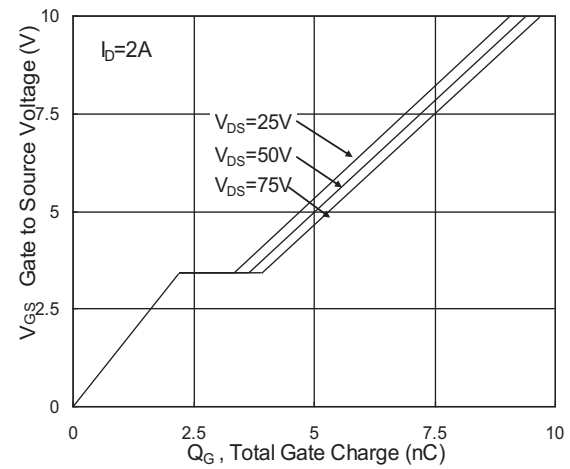


Fig.4 Gate-Charge Characteristics

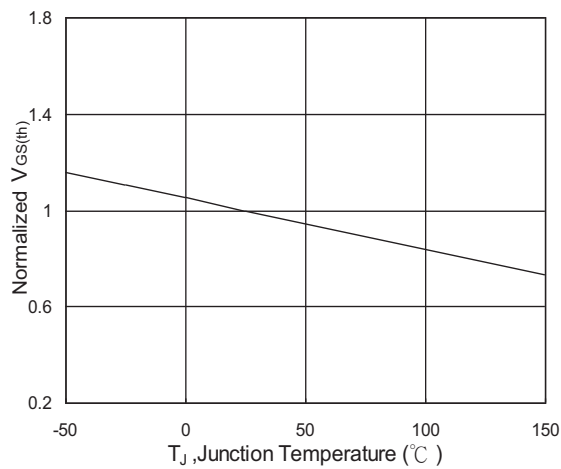


Fig.5 Normalized V_{GS(th)} vs. T_J

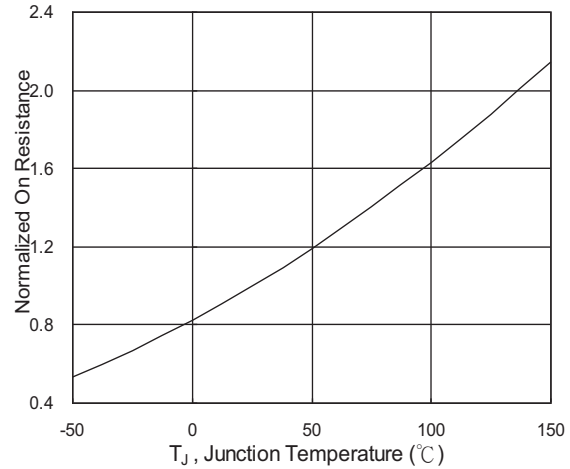


Fig.6 Normalized R_{DS(on)} vs. T_J

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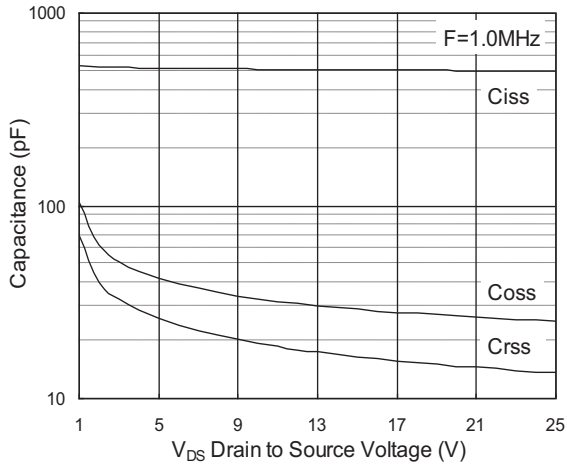


Fig.7 Capacitance

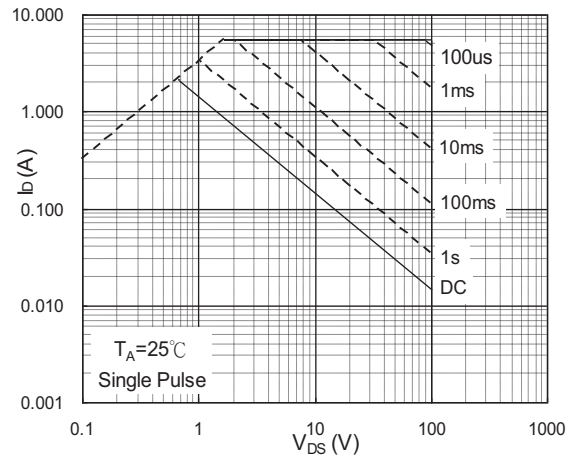


Fig.8 Safe Operating Area

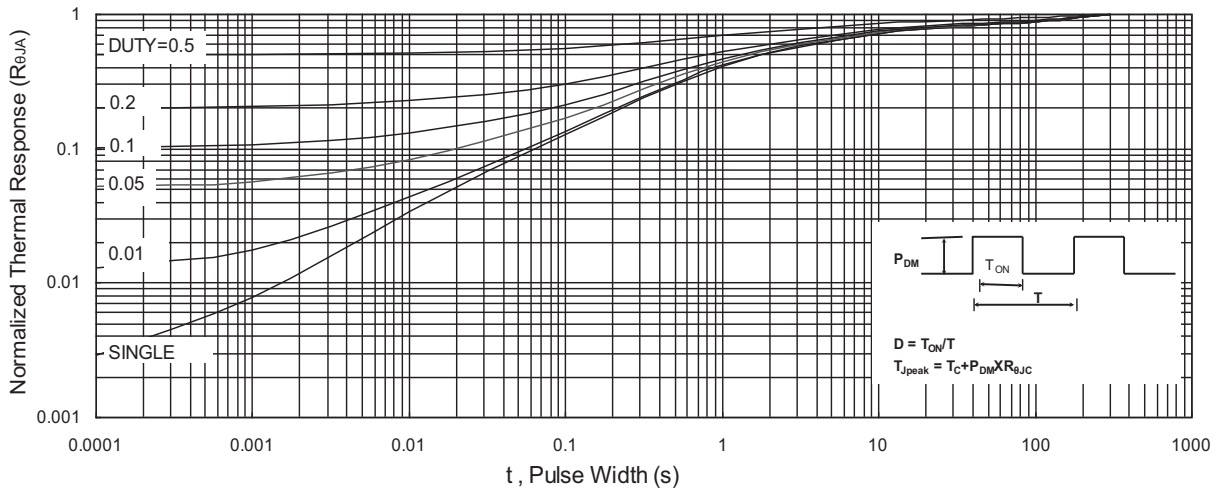


Fig.9 Normalized Maximum Transient Thermal Impedance

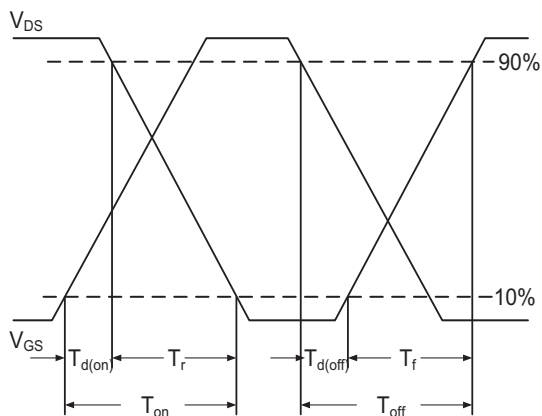


Fig.10 Switching Time Waveform

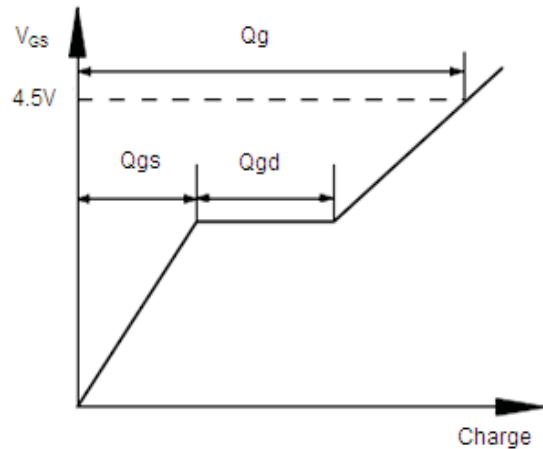


Fig.11 Gate Charge Waveform